

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.
جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید

برای خرید و مشاهده سایر محصولات کلیک کنید



isc®

INCHARGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

BUK455-200A/B

DESCRIPTION

- Drain Source Voltage-
: $V_{DS}=200V(\text{Min})$
- Low $R_{DS(ON)}$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

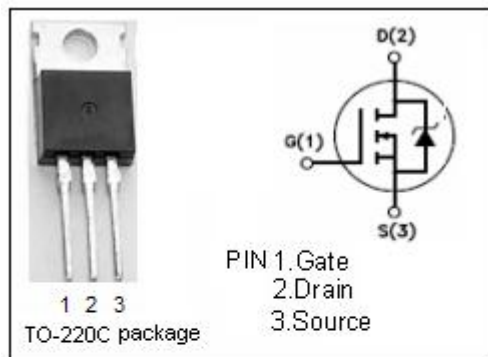
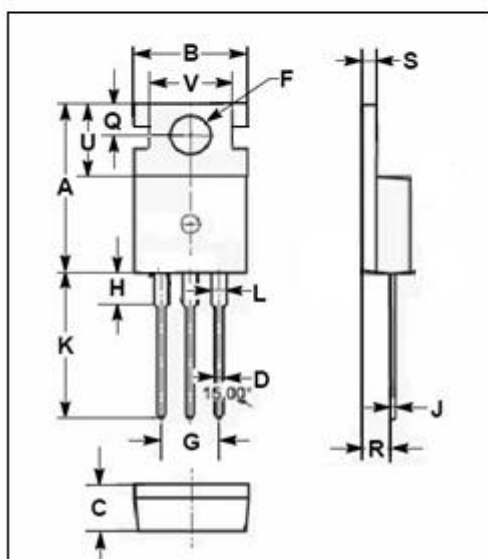
- Designed for Switched Mode Power Supplies (SMPS), motor control, welding, and in general purpose switching resistance application

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage ($V_{GS}=0$)	200	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous @ $TC=25^\circ\text{C}$	BUK455-200A 14	A
		BUK455-200B 13	
P_{tot}	Total Dissipation @ $TC=25^\circ\text{C}$	125	W
T_j	Max. Operating Junction Temperature	175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	175	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.2	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	60	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc N-Channel Mosfet Transistor

BUK455-200A/B

• ELECTRICAL CHARACTERISTICS (T_c=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 0.25mA	200			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =1mA	2.1		4.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =7A			0.23	Ω
		BUK455-200B			0.28	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =200V; V _{GS} = 0			10	uA
V _{SD}	Diode Forward Voltage	I _F =14A; V _{GS} =0			1.5	V
G _{fs}	Forward Transconductance	V _{DS} = 25V; I _D = 7A	6.0			S
t _r	Rise time	V _{GS} =10V; I _D =3A; R _{GS} =50 Ω		35	60	ns
t _{on}	Turn-on time			18	30	ns
t _f	Fall time			35	50	ns
t _{off}	Turn-off time			85	120	ns

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